

80A 1200V Fast recovery diode

1 Description

80A, 1200V Ultrafast Diodes They have a low forward voltage drop and are of planar, silicon nitride passivated, ion-implanted, epitaxial construction. These devices are intended for use as energy steering/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor

2 Features

- Low power loss,
- high efficiency Low forward voltage,
- high current capability High surge capacity
- Super fast recovery times
- high voltage

3 Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

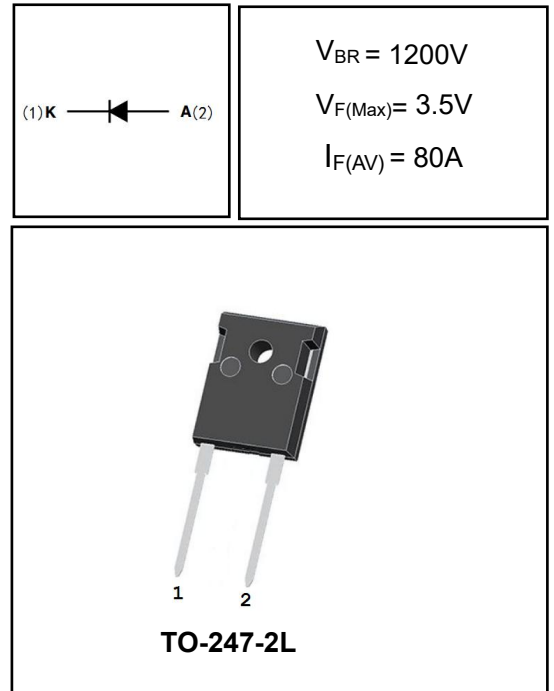
4 Electrical Characteristics

4.1 Absolute Maximum Ratings (T_c=25°C, unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage		V _{RRM}	1200	V
Working Peak Reverse Voltage		V _{RWM}	1200	V
DC Blocking Voltage		V _R	1200	V
Average Rectified Forward Current	T _c =135°C	I _{F(AV)}	80	A
Repetitive Peak Surge Current		I _{FRM}	120	A
Nonrepetitive Peak Surge Current	tp=8.3ms	I _{FSM}	600	A
Avalanche Energy	L=1mH	E _{AS}	200	mJ
Operating Junction Temperature Range		T _j	-55~175	°C
Storage Temperature Range		T _{stg}	-55~175	°C

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	R _{thJC}	0.8	°C/W



4.3 Electrical Characteristics (Tc=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous Forward Voltage	V _F	I _F = 30A	-	2.1	-	V
		I _F = 50A	-	2.3	-	V
		I _F = 60A	-	2.4	-	V
		I _F = 80A,	-	2.8	3.5	V
		I _F = 80A, T _C = 150°C	-	2.3	-	V
		I _F = 120A	-	3.2	-	V
		I _F = 160A	-	3.4	-	V
Maximum Instantaneous Reverse	I _R	V _R = 1200V	-	-	5	uA
		V _R = 1200V, T _C = 150°C	-	-	5	mA
Maximum Reverse Recovery Time	t _{rr}	I _F = 0.5A, I _R =1A, I _{RR} = 0.25A	-	55	80	ns
Diode reverse recovery time	t _{rr}	T _j =25°C V _R =600V I _F =80A di _F /dt=300A/uS	--	115	--	nS
Diode peak reverse recovery current	I _{rrm}		--	10	--	A
Diode reverse recover charge	Q _{rr}		--	630	--	nC
Total capacitance	C _{tot}	V _R =0V f=1MHz	-	600	-	pF
DC Blocking Voltage	V _{BR}	I _R =100uA	1200	1360	-	V

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300µs, D = 2%).

I_R = Instantaneous reverse current.

RθJC = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

5 Typical characteristics diagrams

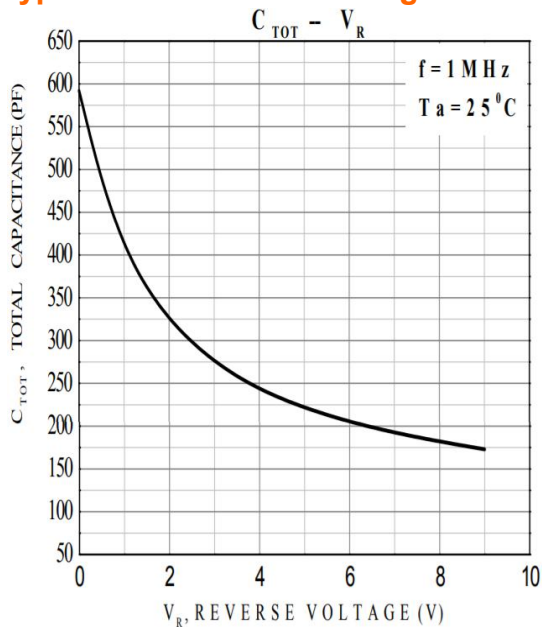


FIGURE 1. Total capacitance vs Voltage

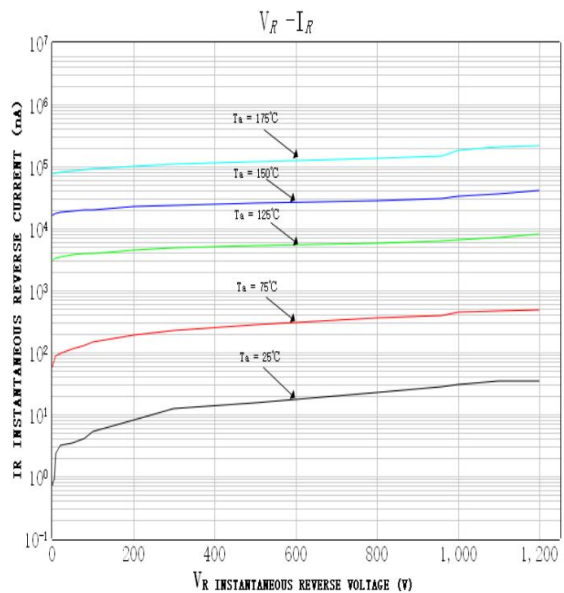


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

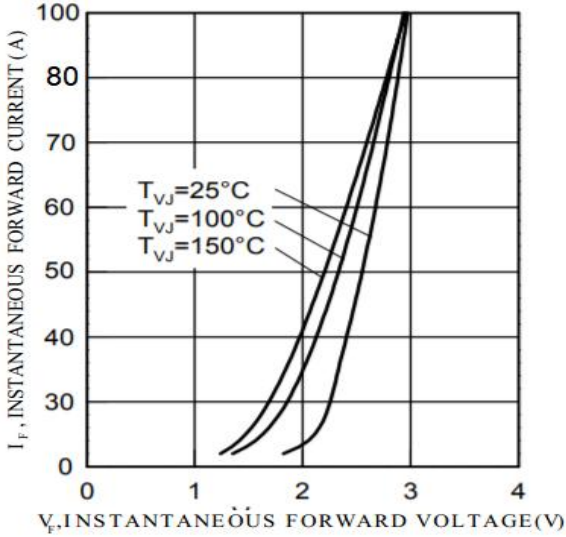


FIGURE 3. FORWARD CURRENT vs FORWARD VOLTAGE

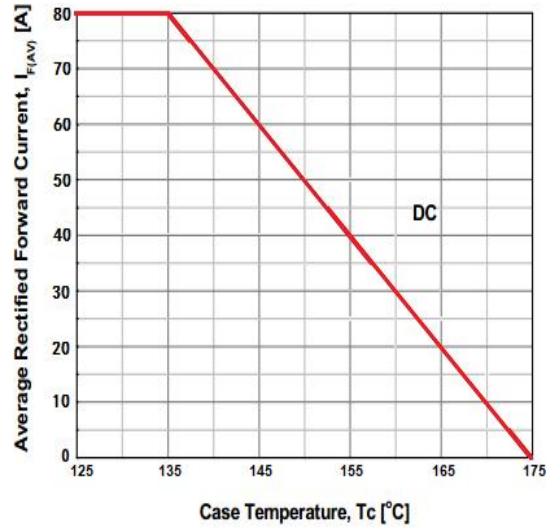


FIGURE 4. CURRENT DERATING CURVE

6 Typical Test Circuit and Waveform

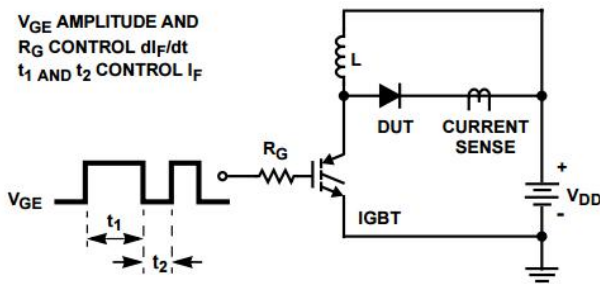


FIGURE 5. t_{rr} TEST CIRCUIT

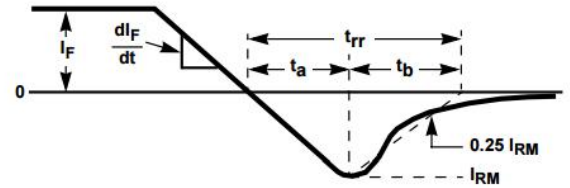


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

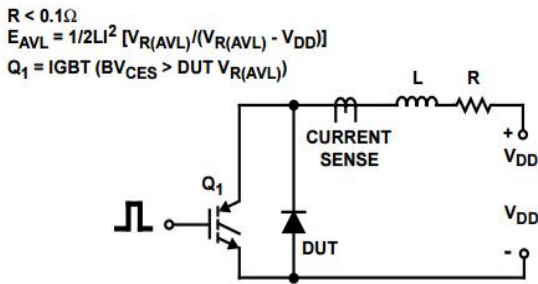


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

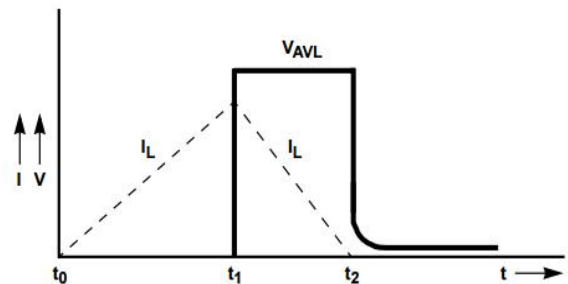
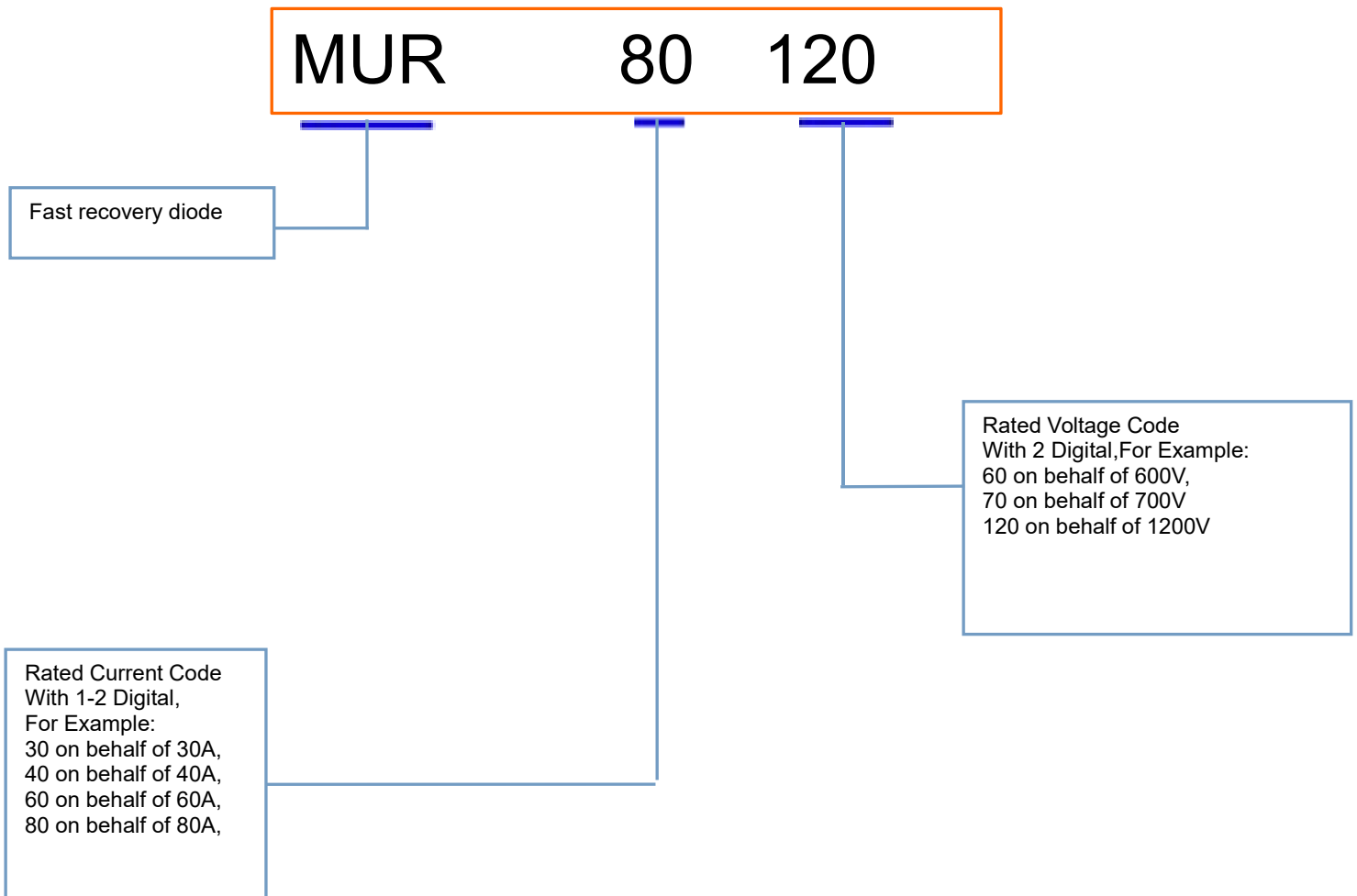


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

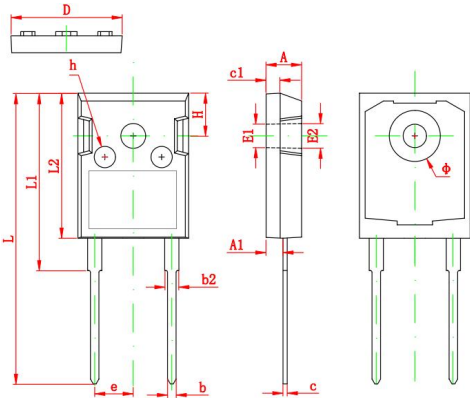
7 Product Names Rules



8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MUR80120	TO-247-2L	MUR80120	Pb-free	Tube	300/box

9 Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012

10 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Jiangsu Donghai Semiconductor Co.,Ltd. products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2017.07.20	1.0	Original	
2022.01.01	1.1	Modify company name	all